THIN SOLID FILMS VOLUME 231, NUMBERS 1–2, AUGUST 25, 1993

Contents

Contents v

Preface vii

Reflection high energy electron diffraction measurements of molecular beam epitaxially grown GaAs and InGaAs on GaAs(111) 1
A. M. Dabiran, P. I. Cohen, J. E. Angelo and W. W. Gerberich (Minneapolis, MN, USA)

Growth of semiconductor heterostructures on patterned substrates: defect reduction and nanostructures 8
A. Madhukar (Los Angeles, CA, USA)

Surfactant-mediated molecular beam epitaxy of strained layer semiconductor heterostructures 43
E. Tournié (Stuttgart, Germany) and K. H. Ploog (Berlin, Germany)

Molecular beam epitaxial GaAs grown at low temperatures 61
D. C. Look (Dayton, OH, USA)

Molecular beam epitaxy for high electron mobility modulation-doped two-dimensional electron gases 74
M. R. Melloch (West Lafayette, IN, USA)

Transport of quasi-two-dimensional electrons in heterojunction field effect transistors 86
W. T. Masselink (Yorktown Heights, NY, USA)

Pseudomorphic InGaAs high electron mobility transistors 95
J. M. Ballingall, P. A. Martin, J. Mazurowski, P. Ho, P. C. Chao, P. M. Smith and K. H. G. Duh (Syracuse, NY, USA)

A review of III–V semiconductor based metal–insulator–semiconductor structures and devices 107
D. S. L. Mui, Z. Wang and H. Morkoç (Urbana, IL, USA)

Si/SiGe heterostructures and devices 125
G. L. Zhou and H. Morkoç (Urbana, IL, USA)

Growth of high quality AlGaAs/GaAs heterostructures by molecular beam epitaxy for photonic and electronic device applications 143
N. Chand (Murray Hill, NJ, USA)

Gas source molecular beam epitaxial growth and device applications in $In_{0.5}Ga_{0.5}P$ and $In_{0.5}Al_{0.5}P$ heterostructures ... 158
J. M. Kuo (Murray Hill, NJ, USA)

Gas source molecular beam epitaxial growth and characterization of 600–660 nm GaInP/AlInP double-heterostructure lasers 173
K. Kishino, A. Kikuchi, I. Nomura and Y. Kaneko (Tokyo, Japan)

The molecular beam epitaxial growth of wide gap II–VI injection lasers and light-emitting diodes 190
R. L. Gunshor (West Lafayette, IN, USA), A. V. Nurmikko (Providence, RI, USA) and N. Otsuka (West Lafayette, IN, USA)

Progress and prospects for GaN and the III–V nitride semiconductors 197
S. Strite, M. E. Lin and H. Morkoç (Urbana, IL, USA)

Author Index 211

Subject Index 213

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